

# TransEON

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Edmonton, AB, Canada

## TransEON Announces MPW Run for 300 nm GaN MOS Platform in Q4 2026

TransEON Inc., a Canadian pure-play GaN foundry, has announced plans to schedule its first MPW run for Q4 2026 using its 300-GaN-MOS process. This platform enables fabrication of cutting-edge transistors and MMICs with significant benefits over existing GaN HEMT technology, including higher RF power density, improved linearity, faster cycle times, and greater development flexibility.

The process features a 300 nm gate length and offers 50 V operation with <10% current collapse under quiescent bias, delivering excellent power and gain for applications up to 30 GHz. It includes standard MMIC features to provide turnkey functionality in existing GaN applications, including through-substrate vias, integrated passives, Au-plated microstrip on thinned SiC, non-linear transistor models, as well as direct compatibility with Keysight ADS and Microwave Office. Other advantages of this offering include access to advanced packaging capabilities, high-touch design and NRE services, ITAR and ITAR-free compatibility, as well as industry-leading cycle times.

For further engagement, TransEON will be at IMS2026 in Boston, MA from June 9<sup>th</sup> through June 11<sup>th</sup> at Booth 13082K. One-on-one meetings [can be requested in advance](#).

To learn more about TransEON and the 300-GaN-MOS process, please [subscribe for email updates](#) or reach out directly to [info@transeon.ca](mailto:info@transeon.ca).

